

ENSC Batch No. \_\_\_\_\_ Wafers Started \_\_\_\_\_ Date \_\_\_\_\_  
 Material \_\_\_\_\_ Orientation \_\_\_\_\_ Size \_\_\_\_\_ Thickness \_\_\_\_\_  
 Resistivity \_\_\_\_\_ Type \_\_\_\_\_  
 Wafer Vendor \_\_\_\_\_ Vendor Batch # \_\_\_\_\_ SFU P.O. \_\_\_\_\_

Process Step #	Process Conditions	Oper & Wafer #	Comments
_____A	<b>RCA SC-1 Clean (Organics)</b> Temp = 80 +/- 5C Time = 10 minutes DI H2O 5 parts (1000mL) NH4OH, 30% 1 part (200 mL) H2O2, 50% 1 part (200 mL)* *Volumes are sufficient to cover 8 wafers in dippers in 2000 mL glass beaker, major flats up.		Hydrate wafers in DI water before placing in SC-1. Heat water for SC-1. Add NH4OH and then H2O2. Stabilize temperature. Remove wafers from water, place in SC-1, and start timing if temp in range.
_____B	<b>DI Water Rinse</b> > 3 minutes in running DI water		
_____C	<b>HF Dip (Native Oxide Strip)</b> Temp = Room temp Time = 30 seconds DI H2O 100 parts (1600 mL)* HF 1 part (16 mL) *Volumes sufficient to cover 8 wafers in dippers in a 2 L plastic beaker, major flats up.		This is the modified step. Either leave out this step completely or reduce concentration from 10:1 to 100:1 as shown.
_____D	<b>DI Water Rinse</b> > 3 minutes in running DI water		
_____E	<b>RCA SC-2 Clean (Metals)</b> Temp = 80 +/- 5C Time = 10 minutes DI H2O 6 parts (1050 mL) HCl 1 part (175 mL) H2O2 1 part (175 mL)* *Volumes for 2 L glass beaker		Heat the water. Add HCl and then H2O2. Note that the addition of the HCl can raise the temperature of the solution significantly. Stabilize the temperature. Remove wafers from rinse, place in SC-2, and start timing if temp in range.
_____F	<b>DI Water Dump Rinse</b> > 5 min in beaker of running DI H2O. Dump H2O. Repeat twice		
_____G	<b>Spin Dry</b> Spin at max RPM until dry (false colours disappear). Check for water on back. Repeat spin or blow with dry N2 if needed.		